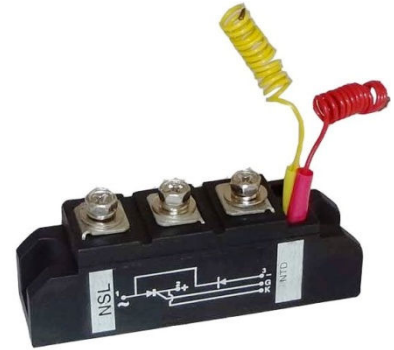


Thyristor – Diode Module

Features

- Improved glass passivation for high reliability
- Exceptional stability at high temperatures
- High di/dt and dv/dt capabilities
- Low thermal resistance

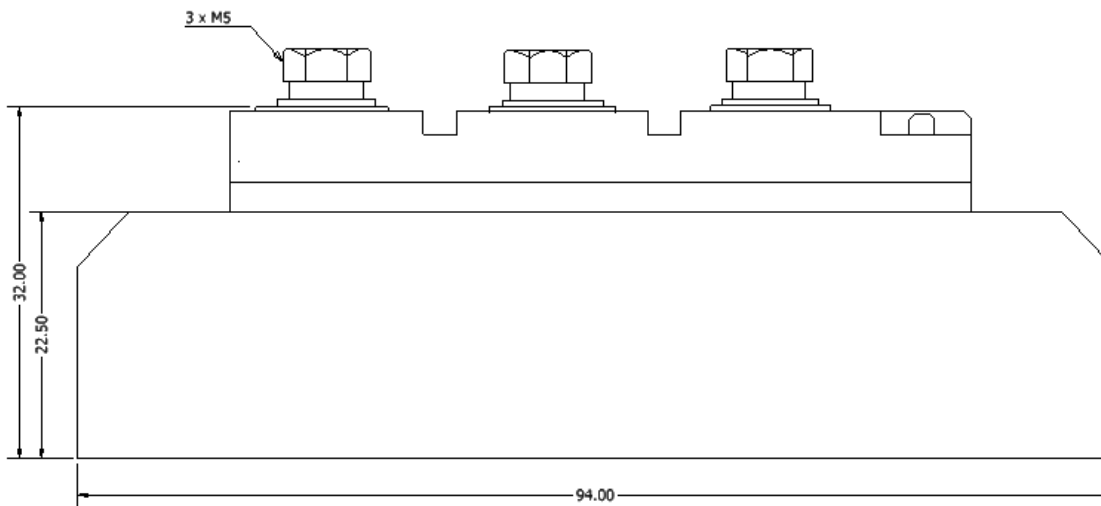
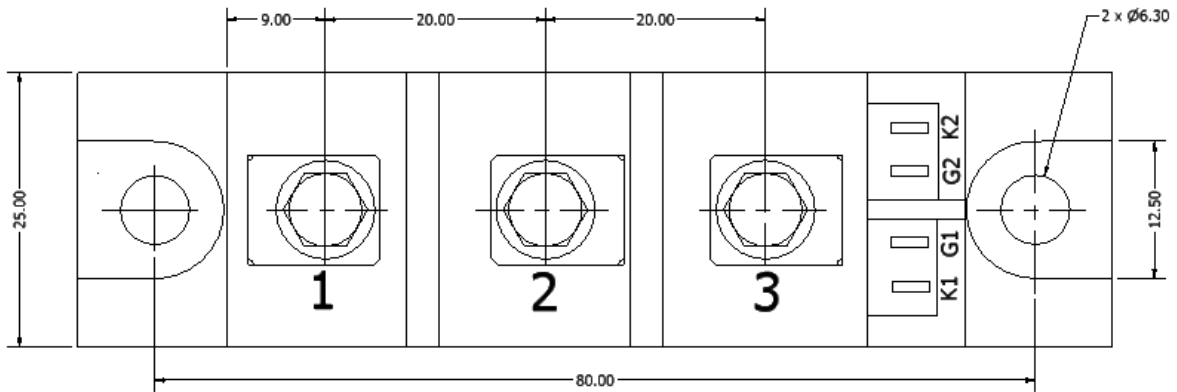
| Maximum Ratings ($T_A = 25^{\circ}\text{C}$ unless otherwise noted) | | | |
|--|--------------|--------|-----------------------|
| Parameter | Symbol | Values | Units |
| Maximum average forward current @ $T_J = 85^{\circ}\text{C}$ | $I_{F(AV)}$ | 130 | A |
| Maximum average RMS forward current | $I_{F(RMS)}$ | 300 | A |
| Maximum non-repetitive surge current @ $t = 10\text{ms}$ | I_{FSM} | 3300 | A |
| Maximum I^2t for fusing @ $t = 10\text{ms}$ | I^2t | 51 | kA^2s |



M2 PACKAGE

| Thermal & Mechanical Specifications ($T_A = 25^{\circ}\text{C}$ unless otherwise noted) | | | |
|--|--------------|-------------|----------------------|
| Parameter | Symbol | Values | Units |
| Operating junction temperature range | T_J | -65 to +125 | $^{\circ}\text{C}$ |
| Thermal resistance, junction to case | $R_{th(JC)}$ | 0.18 | $^{\circ}\text{C/W}$ |

| Electrical Characteristics ($T_A = 25^{\circ}\text{C}$ unless otherwise noted) | | | |
|---|--------------|-------------|------------------------|
| Parameter | Symbol | Values | Units |
| Maximum average on-state current | $I_{T(max)}$ | 130 | A |
| Maximum repetitive peak reverse voltage range | V_{RRM} | 200 to 1600 | V |
| Forward voltage drop | V_{FM} | 1.55 | V |
| Gate current required to trigger | I_{GT} | 150 | mA |
| Gate voltage required to trigger | V_{GT} | 2.5 | V |
| Holding current range | I_H | 200 | mA |
| Maximum latching current | I_L | 300 | mA |
| Critical rate of rise of off-state voltage | dv/dt | 1000 | $\text{V}/\mu\text{s}$ |
| RMS isolated voltage | V_{ISO} | 3500 | V |



ALL DIMENSIONS IN MM

Diode Configuration

